

# Franky Juanda Lumbantoruan

## List of Publications by Year in descending order

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9  
papers

111  
citations

1684188  
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1872680  
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docs citations

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times ranked

186  
citing authors

#	ARTICLE	IF	CITATIONS
1	Analysis of Leakage Current Mechanism for Ni/Au Schottky Contact on InAlGaN/GaN HEMT. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700741.	1.8	8
2	High-Performance Normally-OFF GaN MIS-HEMTs Using Hybrid Ferroelectric Charge Trap Gate Stack (FEG-HEMT) for Power Device Applications. IEEE Electron Device Letters, 2018, 39, 991-994.	3.9	35
3	High-Performance LPCVD-SiN <sub>x</sub> /InAlGaN/GaN MIS-HEMTs With 850-V 0.98- $\text{ext}\{m\}\{\Omega\}$ $\text{cm}^2$ for Power Device Applications. IEEE Journal of the Electron Devices Society, 2018, 6, 1136-1141.	2.1	18
4	A Novel Digital Etch Technique for p-GaN Gate HEMT. , 2018, , .		4
5	InGaAs Junctionless FinFETs with Self-Aligned Ni-InGaAs S/D. IEEE Journal of the Electron Devices Society, 2018, , 1-1.	2.1	10
6	RF loss mechanisms in GaN-based high-electron-mobility-transistor on silicon: Role of an inversion channel at the AlN/Si interface. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600944.	1.8	30
7	Buffer-optimized improvement in RF loss of AlGaIn/GaN HEMTs on 4-inch silicon (111). , 2017, , .		2
8	Growth and characterization of high quality N-type GaSb/GaAs heterostructure by IMF growth mode using MOCVD for low power application. Applied Physics Letters, 2017, 111, 162108.	3.3	1
9	Investigation of TMAI preflow to the properties of AlN and GaN film grown on Si(111) by MOCVD. , 2014, , .		3